

	DISEÑO DE UN SISTEMA DE ALMACENAMIENTO DE ENERGÍA HÍBRIDO BASADO EN BATERÍAS Y SUPERCONDENSADORES PARA SU INTEGRACIÓN EN MICROREDES ELÉCTRICAS
	AUTOR: Isaac Gil Mera
	TUTOR: Sergio Vázquez Pérez

CAPÍTULO 7. ANEXOS



**DISEÑO DE UN SISTEMA DE ALMACENAMIENTO DE ENERGÍA HÍBRIDO
BASADO EN BATERÍAS Y SUPERCONDENSADORES PARA SU
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1. SELECCIÓN DE DRIVERS CON DRIVERSEL™

Driver Select Tool

Preselect	Vcc = 1200 V	
Product	SEMITRANS (106)	
Device	SKM300GB125D	
Number of IGBT Modules	1	
Switching Frequency fsw	10	kHz
Applied Gate Resistor	3	Ohm
Update		

Result

Driver Channels	2
Collector Emitter Voltage	1200 V
Required Average Current	19 mA
Gate Charge	1.9 mC

Driver

Name	I _{out(av)} / mA	I _{out} / A	V _{isol} / kV	V _{ce max} / V	R _{gmin} / Ohm	Channels
1x SKHI22A R or SKHI22B R ⁽¹⁾	40	8	2.5	1200	3.0	2
1x SKHI23/12 R	50	8	2.5	1200	2.7	2
1x SKYPER 32 R or SKYPER 32PRO R	50	15	4.0	1200	1.5	2

Note

1) A: 15V - V_{in}; B: 5V - V_{in}

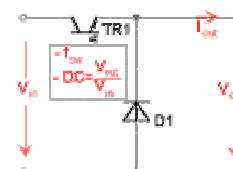


2. ESTUDIO TÉRMICO DE CONVERTIDOR BUCK

Project:

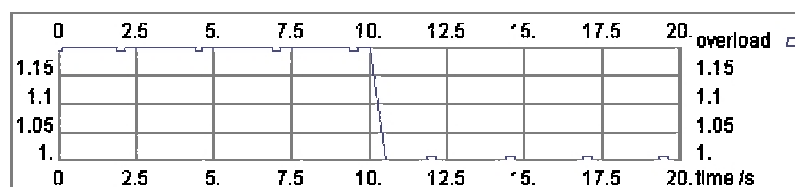
Topology DC/DC

Circuit Buck



Results:

V_{in} 750 V
 I_{in} 16.29 A
 f_{sw} 10 kHz
 Duty Cycle 0.333 (x100%)
 V_{out} 250 V
 I_{out} 46.67 A
 $t_{on\ fwd}$ 0.667
 Overload Factor 1.2
 Overload Duration 10 sec



Overload characteristic

Device:

Product Line **SEMITRANS**
 Device **SKM300GB125D**
 Use Maximum Values No
 Max. Junction Temperature 150

Transistor

$E_{tr} = 27\text{ mJ (@600V)}$
 $V_{CE0.125} = 1.75\text{ V}$
 $r_{CE.125} = 8\text{ mOhm}$
 $V_{CE,sat} = 3.35\text{ V}$
 $I_c = 200.00\text{ A}$
 $R_{th(j-c)} = 0.075\text{ K/W}$
 $R_{th(c-s)} = 0.038\text{ K/W}$

Diode

$E_d = 13\text{ mJ}$
 $V_{T0.125} = 0.9\text{ V}$
 $r_{T.125} = 4.25\text{ mOhm}$
 $V_f = 1.75\text{ V}$
 $I_f = 200.00\text{ A}$
 $R_{th(j-c)} = 0.18\text{ K/W}$

Data set from 2005/08/23

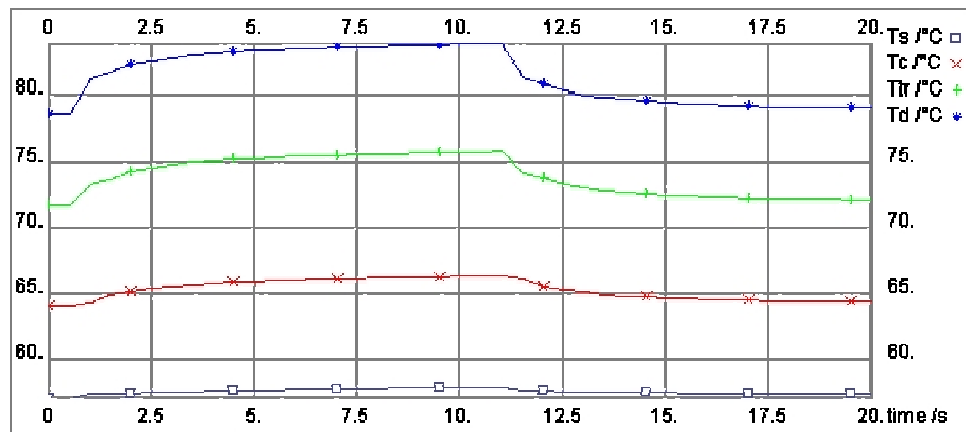
Conditions:

Ambient temperature 40
 Number of switches per heat sink 3
 Number of parallel devices on the same heat sink 1
 Additional power source at this heat sink 0
 Predefined SK-Heat Sink P16_300_168
 Correction Factor 1
 Forced Air Cooling, Flow Rate: 295 m³/h
 $R_{th(s-a)}$ 0.031 K/W

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Calculated losses and temperatures with rated current and at overload:

	Rated Current	Overload
$P_{cond tr}$	30 W	38 W
$P_{sw tr}$	72 W	88 W
P_{tr}	103 W	126 W
$P_{cond d}$	38 W	46 W
$P_{sw d}$	43 W	51 W
P_d	81 W	97 W
P_{tot}	551 W	669 W
T_h	57 °C	58 °C
T_c	64 °C	66 °C
T_{tr}	72 °C	76 °C
T_d	79 °C	84 °C



Temperature characteristic overload current

Evolution:

This configuration seems to be too powerful.

Power device selection:

Name	$I_{out(av)} / mA$	$\hat{I}_{out} / A$	V_{isol} / kV	$V_{ce max} / V$	R_{gmin} / Ohm	Channels
1x SKHI22A R or SKHI22B R ⁽¹⁾	40	8	2.5	1200	3.0	2
1x SKHI23/12 R	50	8	2.5	1200	2.7	2
1x SKYPER 32 R or SKYPER 32PRO R	50	15	4.0	1200	1.5	2

Additional characteristics at given nominal operation conditions with one free parameter (X):

None selected

Note:

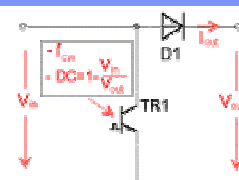
1) A: 15V - Vin; B: 5V - Vin

3. ESTUDIO TÉRMICO DE CONVERTIDOR BOOST

Project

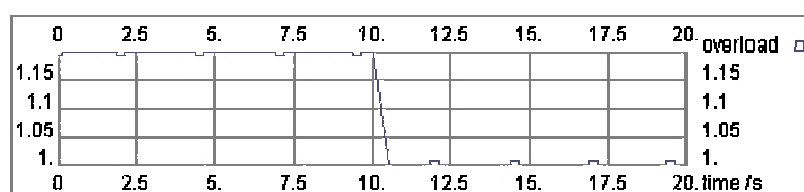
Topology DC/DC

Circuit Boost



Circuit

V_{in} 250 V
 I_{in} 49.08 A
 f_{sw} 10 kHz
 Duty Cycle 0.667 (x100%)
 V_{out} 750 V
 I_{out} 15.56 A
 $t_{on\ fwd}$ 0.333
 Overload Factor 1.2
 Overload Duration 10 sec



Overload characteristic

Device

Product Line SEMITRANS
 Device SKM300GB125D
 Use Maximum Values No
 Max. Junction Temperature 150

Transistor

$E_{tr} = 27\text{ mJ } (\Phi 600V)$
 $V_{CE0.125} = 1.75\text{ V}$
 $r_{c,125} = 8\text{ mOhm}$
 $V_{CE, sat} = 3.35\text{ V}$
 $I_c = 200.00\text{ A}$
 $R_{th(j-c)} = 0.075\text{ K/W}$
 $R_{th(c-s)} = 0.038\text{ K/W}$

Diode

$E_d = 13\text{ mJ}$
 $V_{T0.125} = 0.9\text{ V}$
 $r_{T,125} = 4.25\text{ mOhm}$
 $V_f = 1.75\text{ V}$
 $I_f = 200.00\text{ A}$
 $R_{th(j-c)} = 0.18\text{ K/W}$

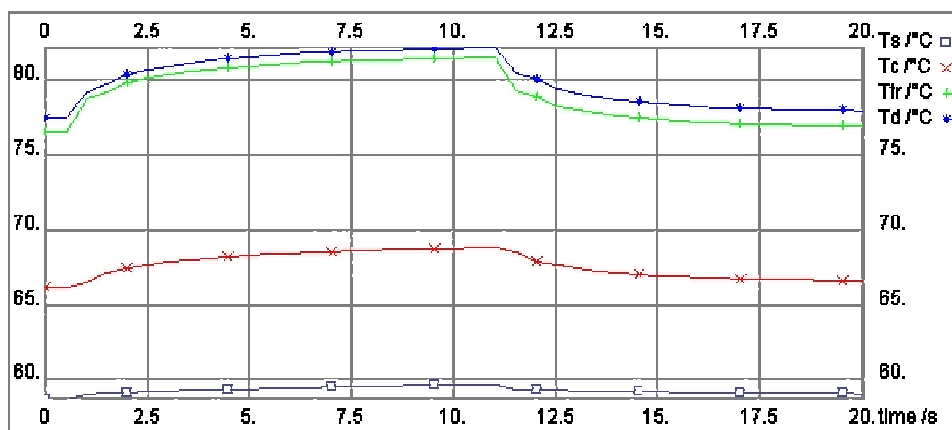
Data set from 2005/08/23

Cooling

Ambient temperature 40
 Number of switches per heat sink 3
 Number of parallel devices on the same heat sink 1
 Additional power source at this heat sink 0
 Predefined SK-Heat Sink P16_300_16B
 Correction Factor 1
 Forced Air Cooling, Flow Rate: 295 m³/h
 $R_{th(s-a)}$ 0.031 K/W

Calculated losses and temperatures with rated current and at overload:

	Rated Current	Overload
$P_{cond tr}$	62 W	78 W
$P_{sw tr}$	75 W	92 W
P_{tr}	137 W	170 W
$P_{cond d}$	19 W	24 W
$P_{sw d}$	43 W	51 W
P_d	63 W	74 W
P_{tot}	601 W	733 W
T_h	59 °C	60 °C
T_c	66 °C	69 °C
T_{tr}	77 °C	82 °C
T_d	78 °C	82 °C



Temperature characteristic overload current

Evaluation:

This configuration seems to be too powerful.

Power electronic suggestion:

Name	$I_{out(av)}$ /mA	I_{out} /A	V_{isol} /kV	$V_{ce max}$ /V	R_{gmin} / Ohm	Channels
1x SKHI22A R or SKHI22B R ⁽¹⁾	40	8	2.5	1200	3.0	2
1x SKHI23/12 R	50	8	2.5	1200	2.7	2
1x SKYPER 32 R or SKYPER 32PRO R	50	15	4.0	1200	1.5	2

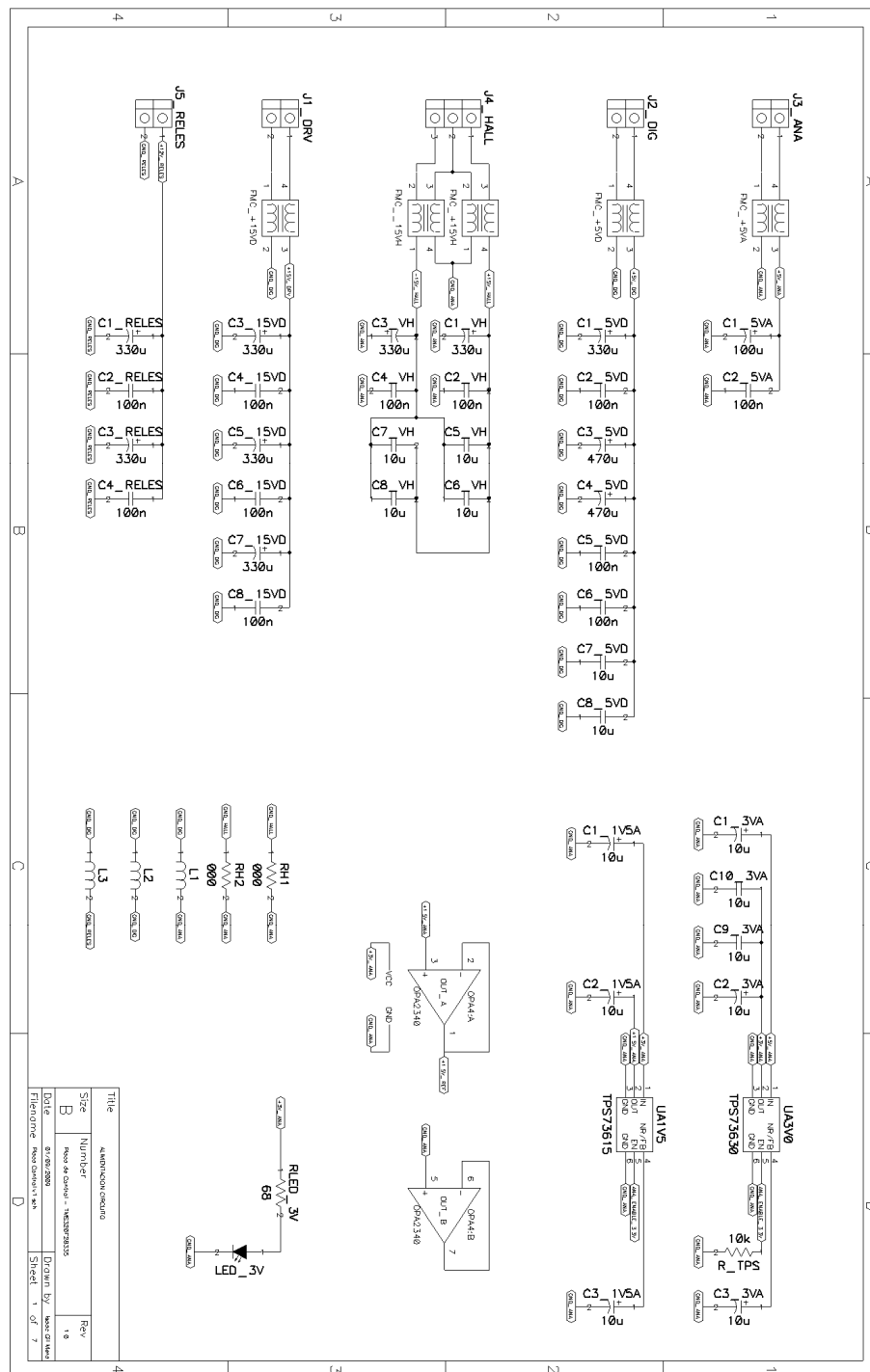
Additional Characteristics at given nominal operation conditions with one free parameter = x:

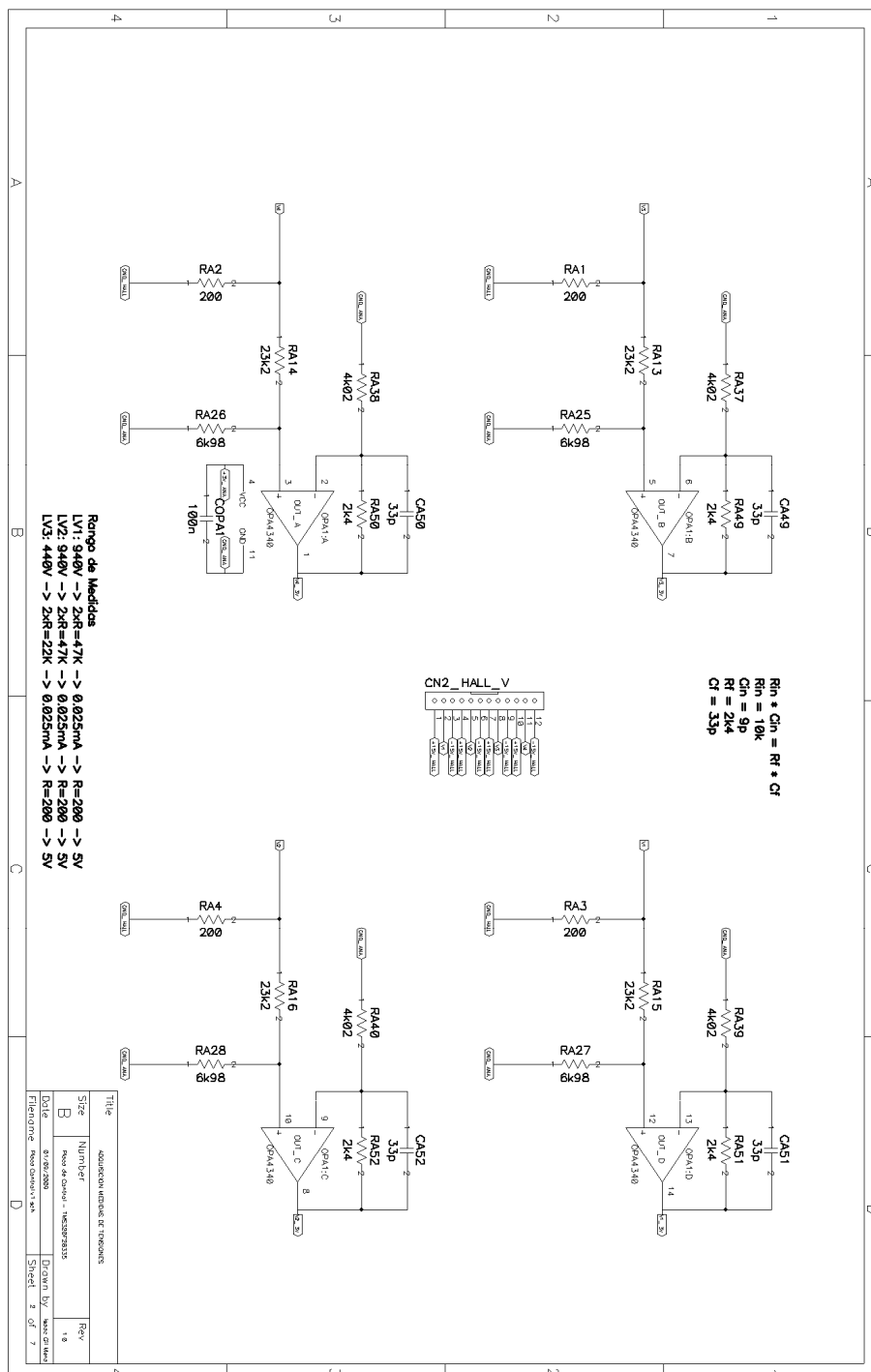
None selected

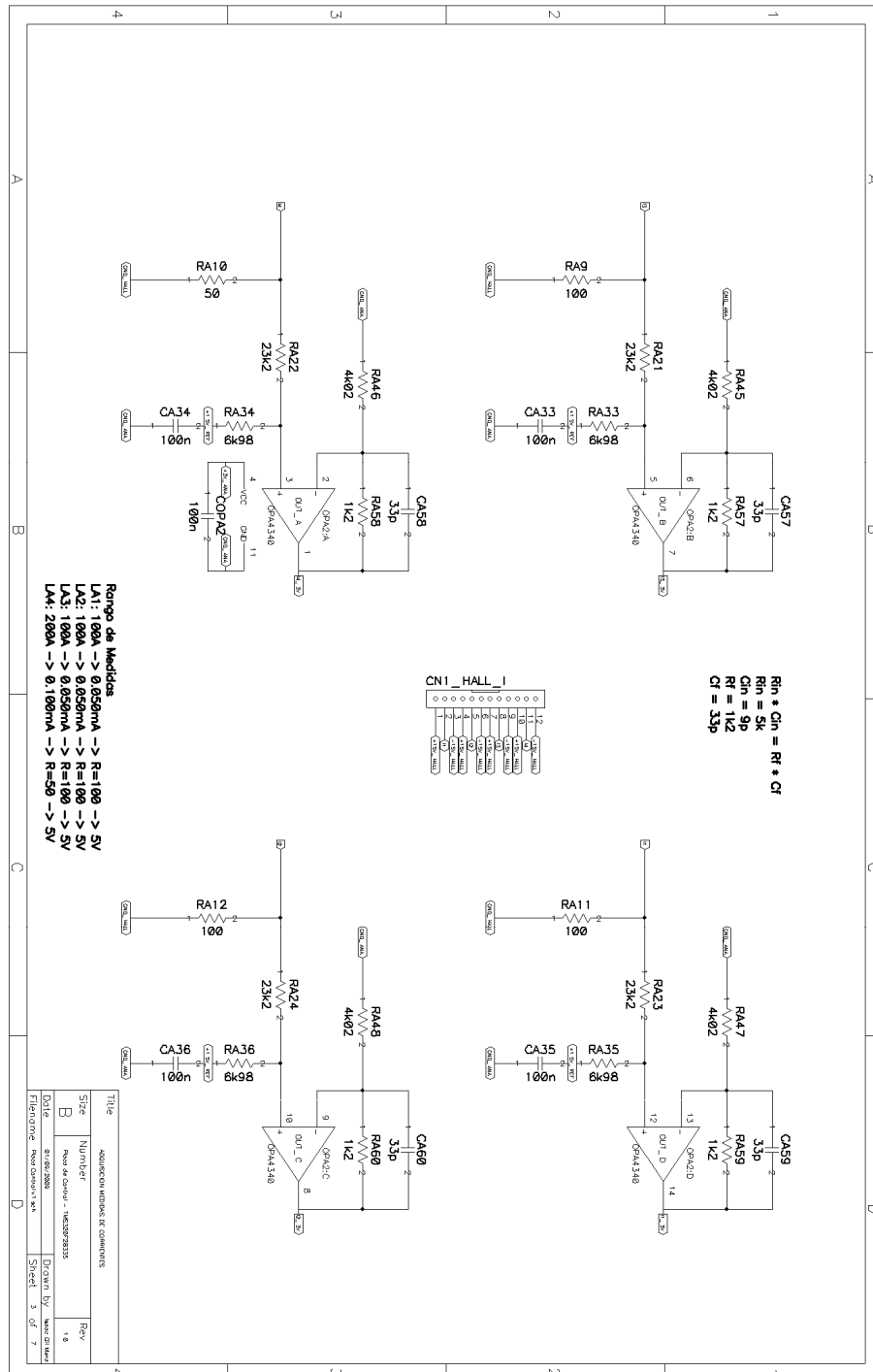
Notes:

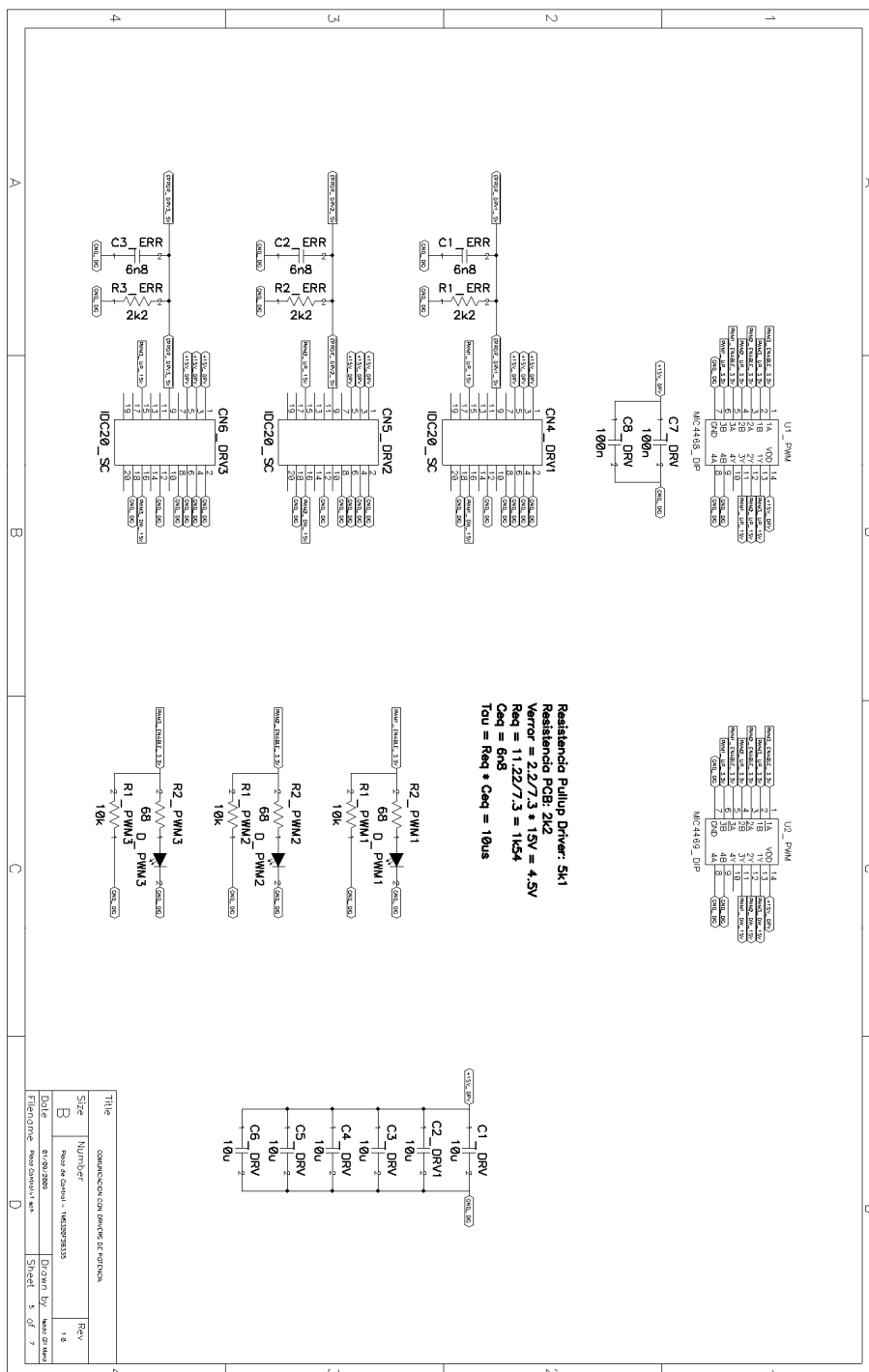
1) A: 15V - Vin; B: 5V - Vin

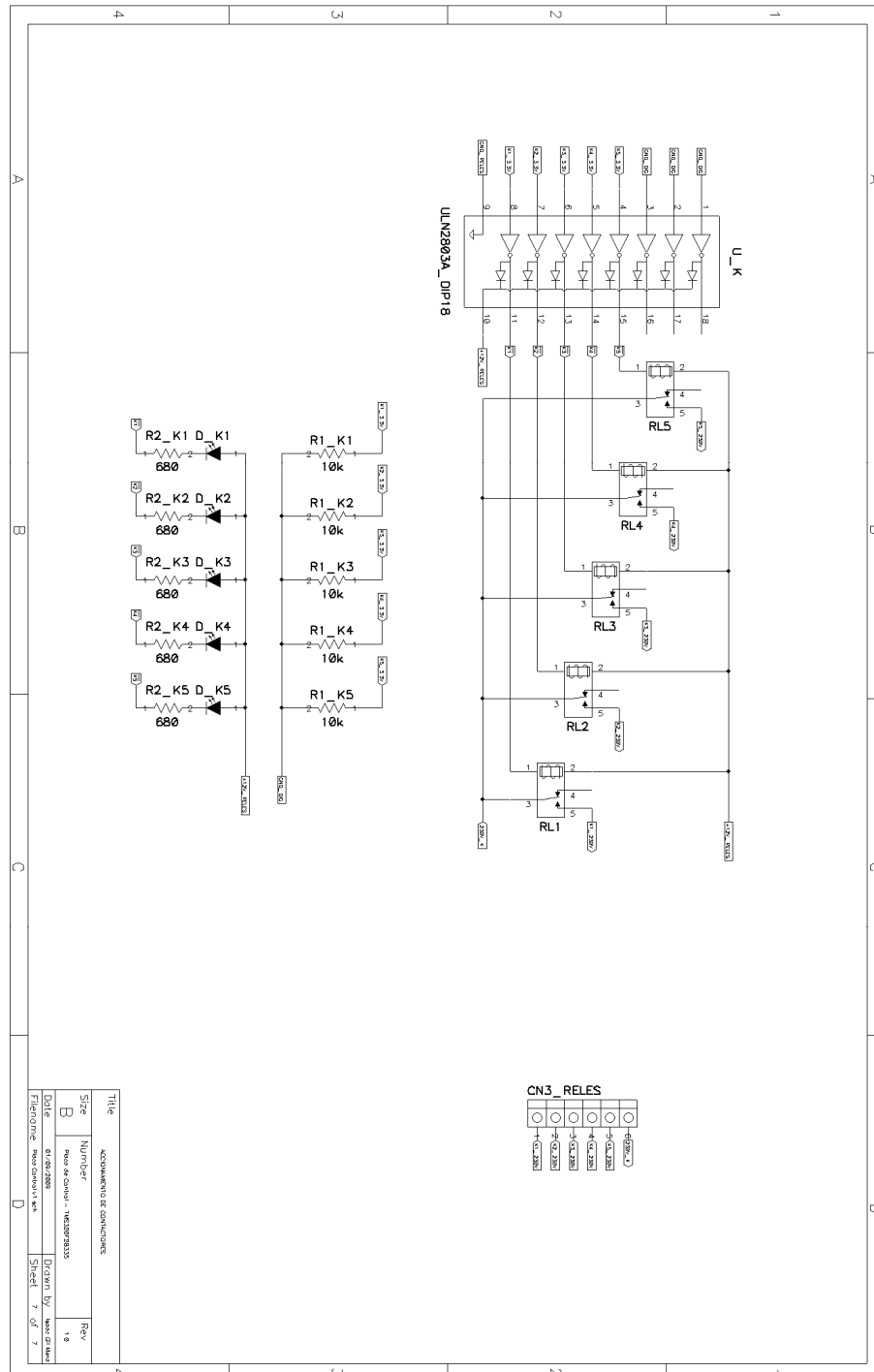
4. ESQUEMÁTICO DE PLACA DE CIRCUITO IMPRESO



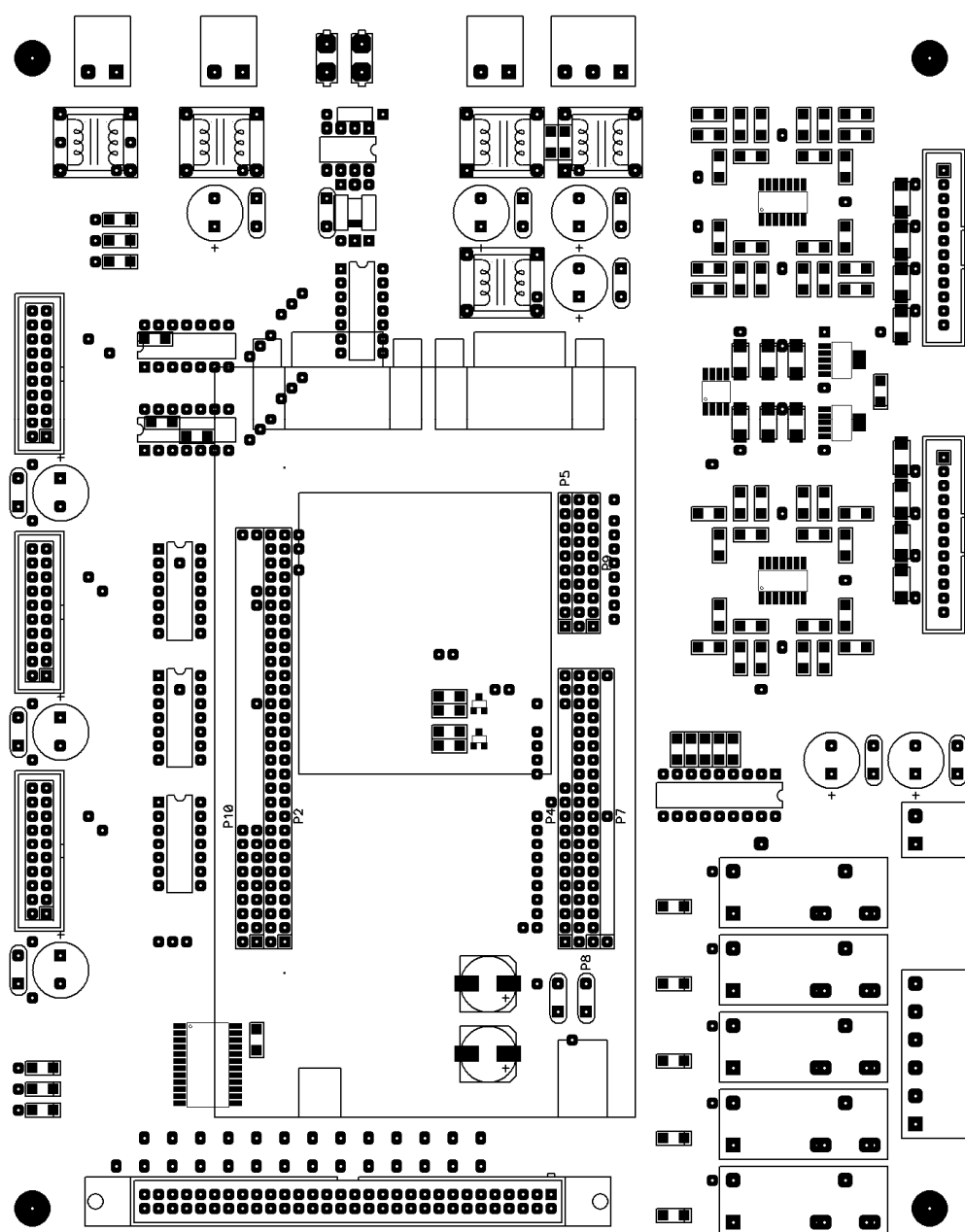




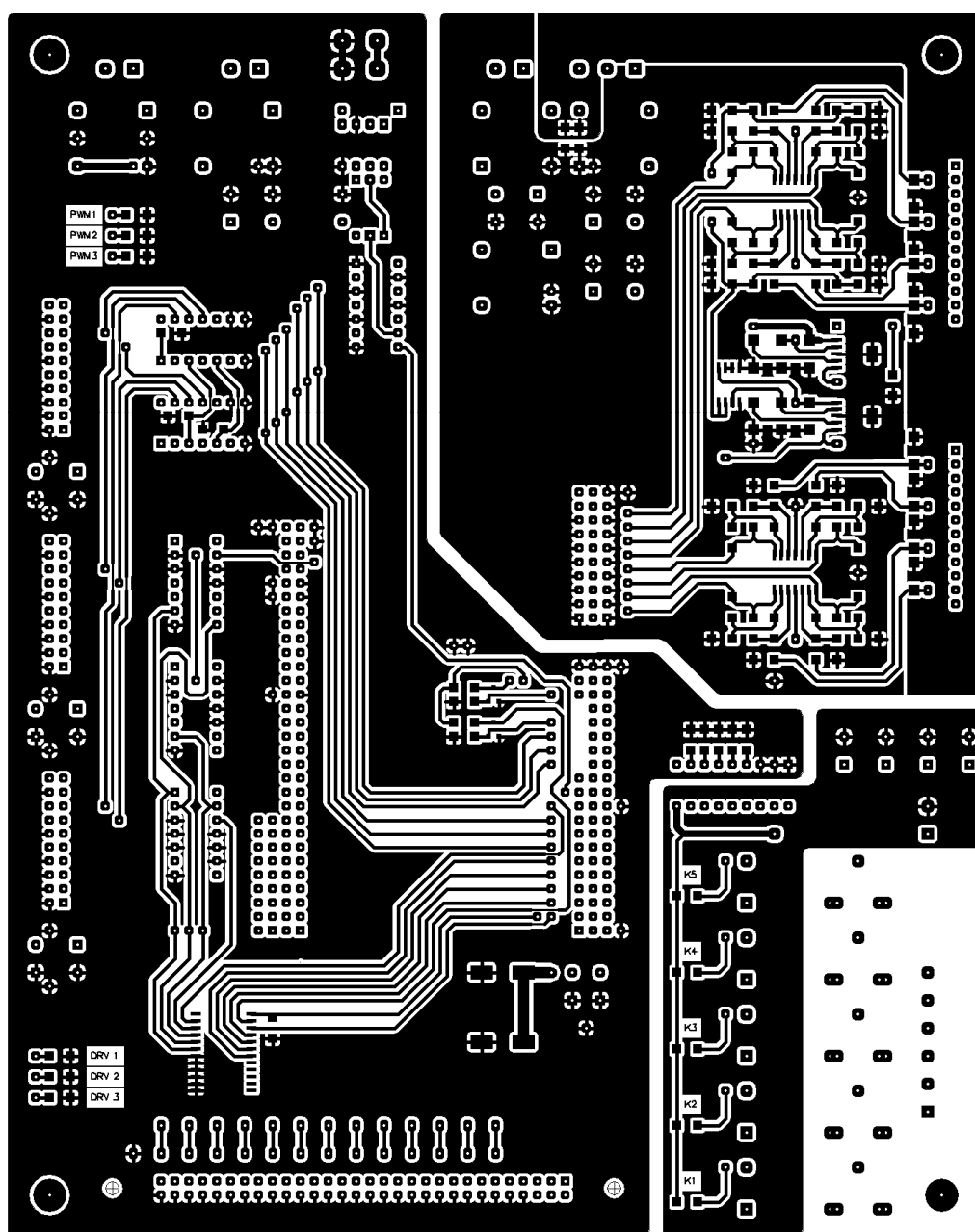




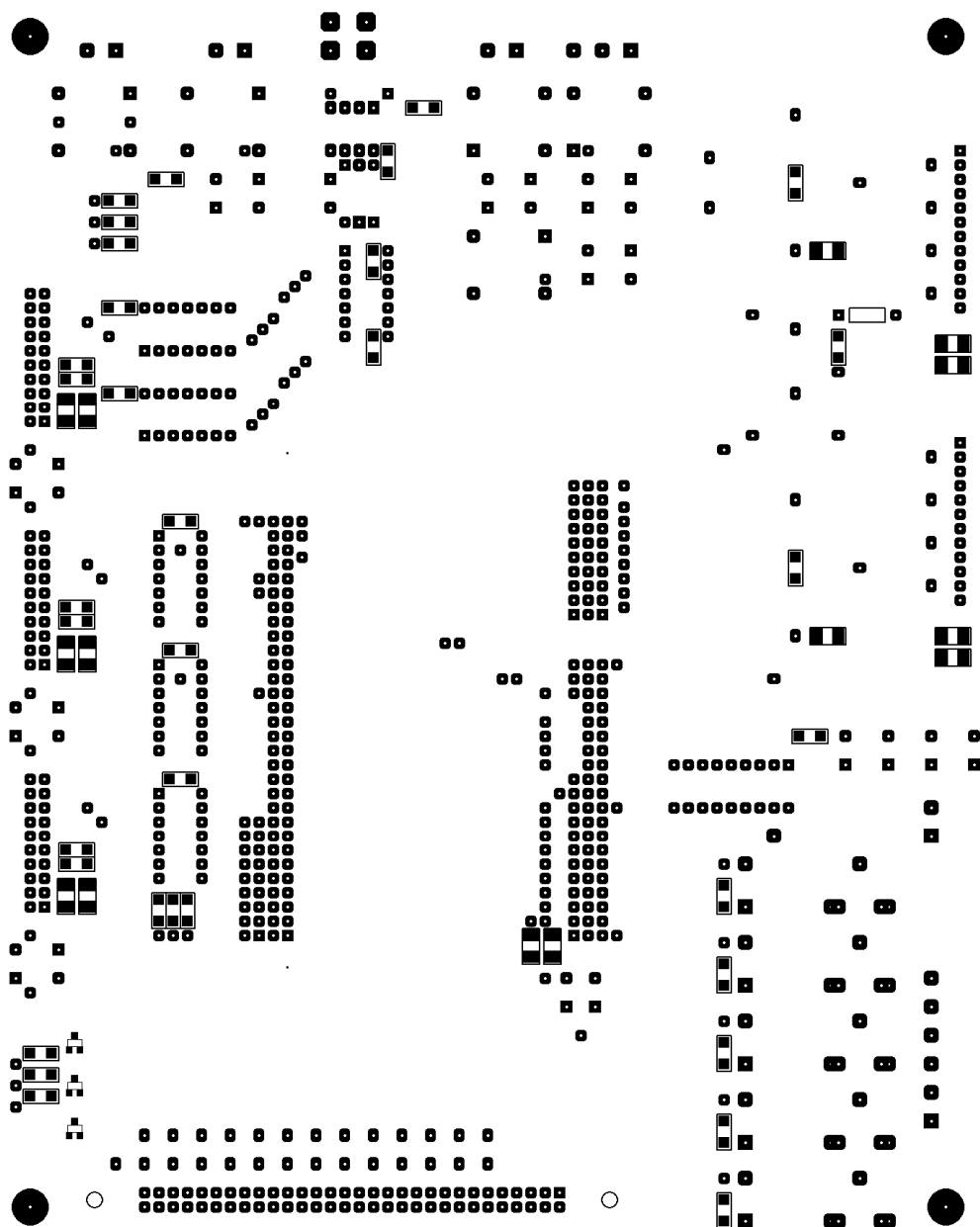
5. LAYOUT DE PLACA DE CIRCUITO IMPRESO



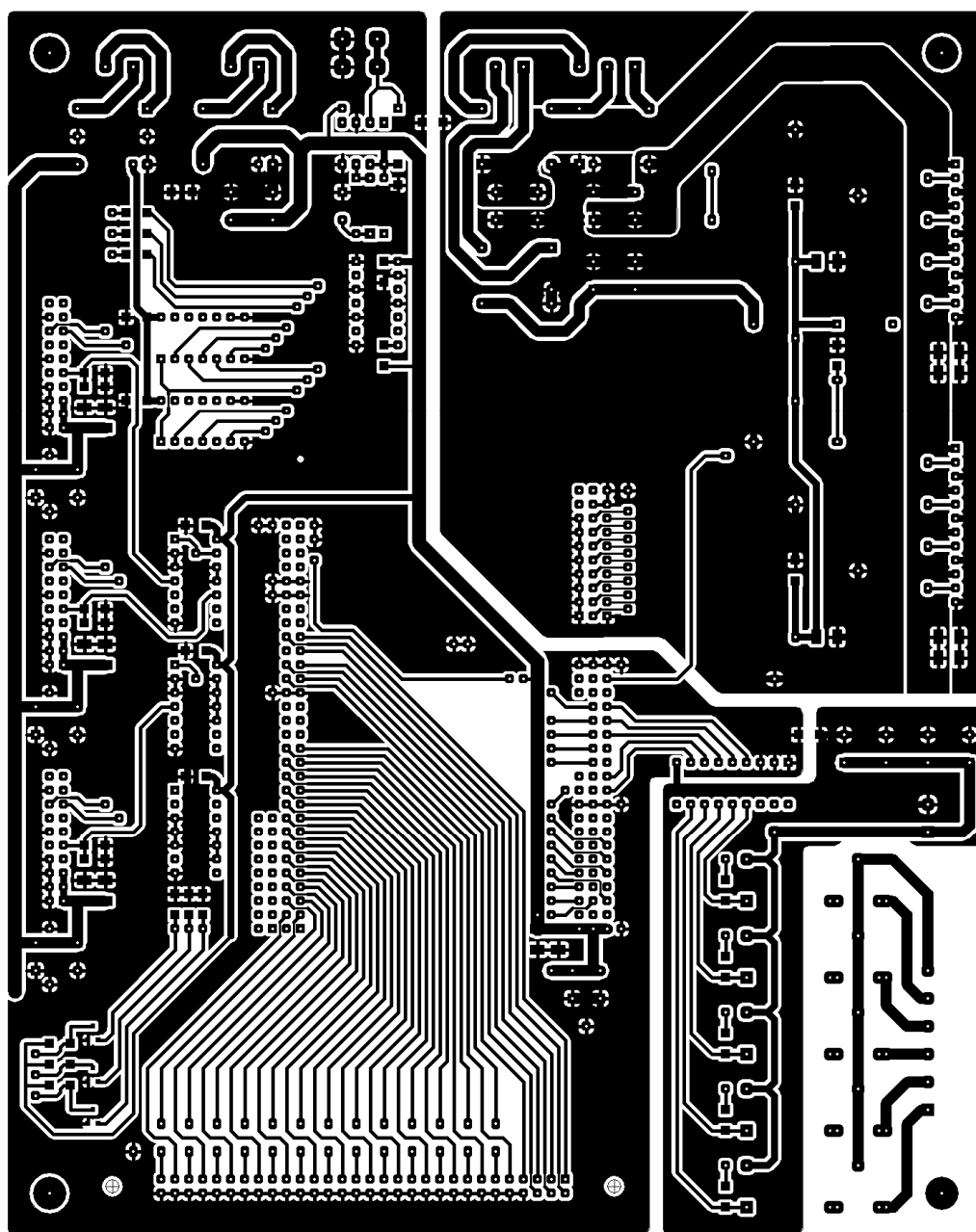
TOP



TOP



BOTTOM



BOTTOM